

• General Description

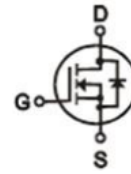
It combines advanced trench MOSFET technology with a low resistance package to provide extremely low $R_{DS(ON)}$.

• Features

- Advance device constructure
- Low $R_{DS(ON)}$ to minimize conduction loss
- Low Gate Charge for fast switching
- Low Thermal resistance

• Application

- Synchronous Rectification for AC-DC/DC-DC converter
- Oring switches
- Power Tools

• Product Summary

 $V_{DS} = 65V$
 $R_{DS(ON)} = 8m\Omega$
 $I_D = 52A$

TO-252
• Ordering Information:

Part NO.	ZMS080N06D
Marking	ZMS080N06
Packing Information	REEL TAPE
Basic ordering unit (pcs)	2500

• Absolute Maximum Ratings (T_C = 25°C)

Parameter	Symbol	Rating	Unit
Drain-Source Voltage	V_{DS}	60	V
Gate-Source Voltage	V_{GS}	±20	V
Continuous Drain Current	$I_{D@TC=25^{\circ}C}$	52	A
	$I_{D@TC=75^{\circ}C}$	40	A
	$I_{D@TC=100^{\circ}C}$	33	A
Pulsed Drain Current ①	I_{DM}	52	A
Total Power Dissipation(TC=25°C)	$P_D@TC=25^{\circ}C$	60	W
Total Power Dissipation(TA=25°C)	$P_D@TA=25^{\circ}C$	2.5	W
Operating Junction Temperature	T_J	-55 to 150	°C
Storage Temperature	T_{STG}	-55 to 150	°C
Single Pulse Avalanche Energy@L=0.1mH	E_{AS}	47	mJ

•Thermal resistance

Parameter	Symbol	Min.	Typ.	Max.	Unit
Thermal resistance, junction - case	R_{thJC}	-	-	2.1	° C/W
Thermal resistance, junction - ambient	R_{thJA}	-	-	62.5	° C/W
Soldering temperature, wavesoldering for 10s	T_{sold}	-	-	265	° C

•Electronic Characteristics

Parameter	Symbol	Condition	Min.	Typ	Max.	Unit
Drain-Source Breakdown Voltage	BV_{DSS}	$V_{GS} = 0V, I_D = 250\mu A$	65			V
Gate Threshold Voltage	$V_{GS(TH)}$	$V_{GS} = V_{DS}, I_D = 250\mu A$	1.2		2.5	V
Drain-Source Leakage Current	I_{DSS}	$V_{DS} = 60V, V_{GS} = 0V$			1.0	μA
Gate- Source Leakage Current	I_{GSS}	$V_{GS} = \pm 20V, V_{DS} = 0V$			± 100	nA
Static Drain-source On Resistance	$R_{DS(ON)}$	$V_{GS} = 10V, I_D = 10A$		8	10	m Ω
		$V_{GS} = 4.5V, I_D = 5A$		11	13	m Ω
Forward Transconductance	g_{FS}	$V_{DS} = 25V, I_D = 10A$		14		S
Source-drain voltage	V_{SD}	$I_S = 10A$			1.28	V

•Electronic Characteristics

Parameter	Symbol	Condition	Min.	Typ	Max.	Unit
Input capacitance	C_{iss}	$f = 1MHz$	-	960	-	pF
Output capacitance	C_{oss}		-	460	-	
Reverse transfer capacitance	C_{rss}		-	9	-	

•Gate Charge characteristics($T_a = 25^\circ C$)

Parameter	Symbol	Condition	Min.	Typ	Max.	Unit
Total gate charge	Q_g	$V_{DD} = 25V$	-	11	-	nC
Gate - Source charge	Q_{gs}	$I_D = 8A$	-	2.2	-	
Gate - Drain charge	Q_{gd}	$V_{GS} = 10V$	-	1.4	-	

Note: ① Pulse Test : Pulse width $\leq 300\mu s$, Duty cycle $\leq 2\%$;

Fig.1 Gate-Charge Characteristics

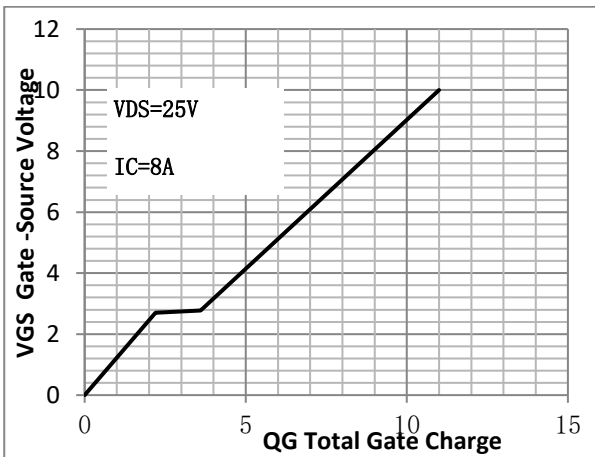


Fig.2 Capacitance Characteristics

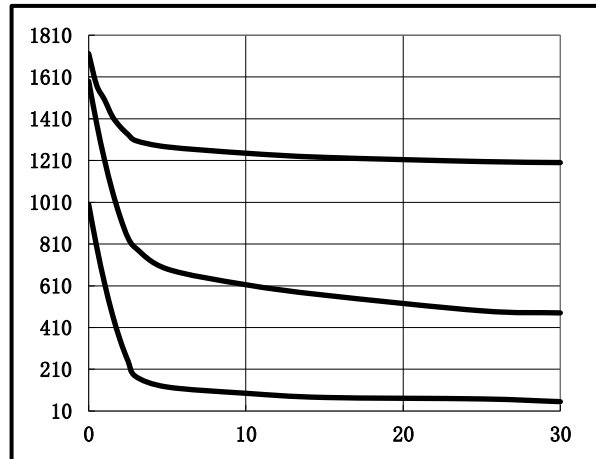


Fig.3 Power Dissipation

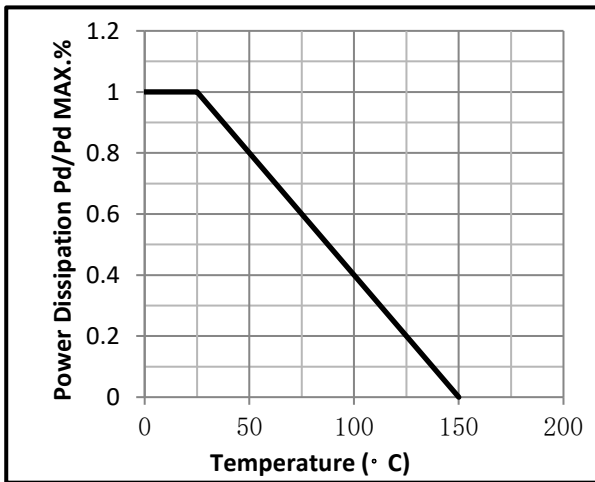


Fig.4 Typical output Characteristics

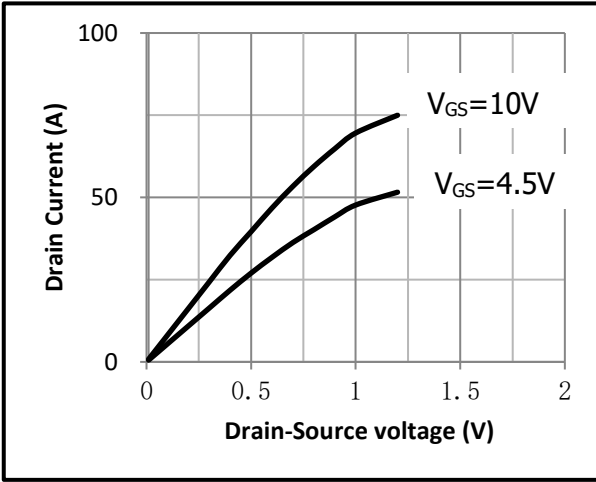


Fig.5 Threshold Voltage V.S Junction Temperature

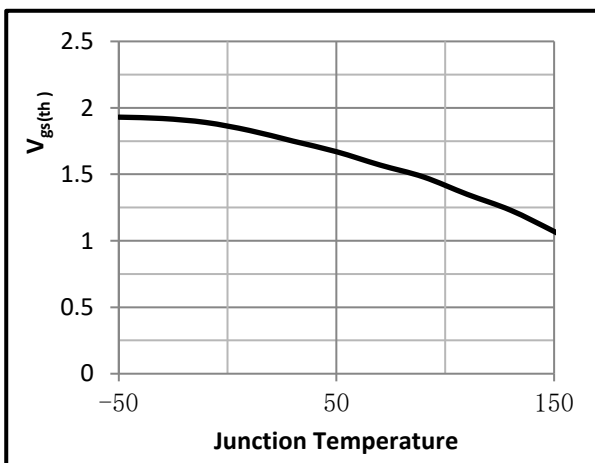


Fig.6 Resistance V.S Drain Current

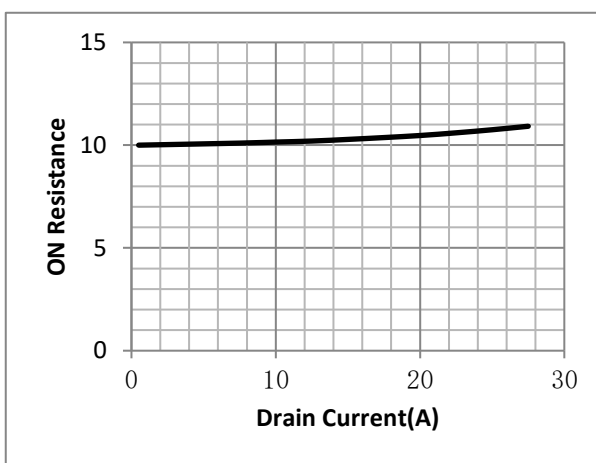


Fig.7 On-Resistance VS Gate Source Voltage

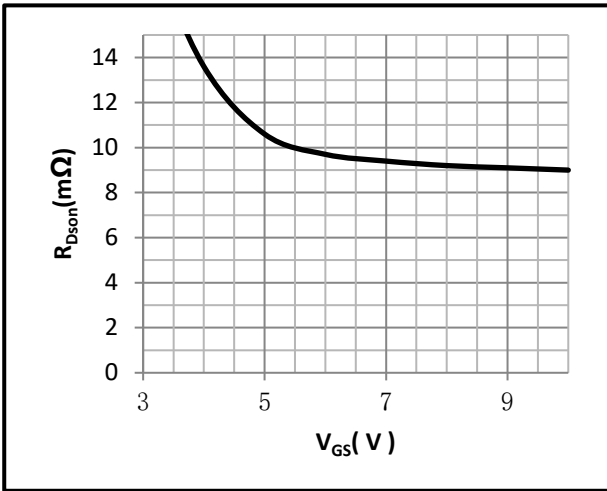


Fig.8 On-Resistance V.S Junction Temperature

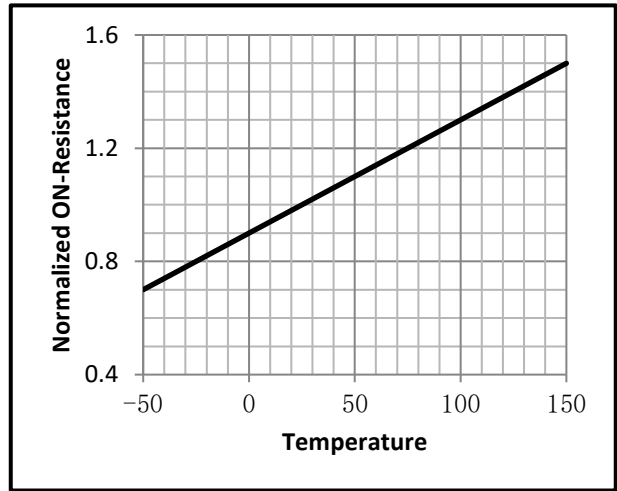


Fig.9 Switching Time Measurement Circuit

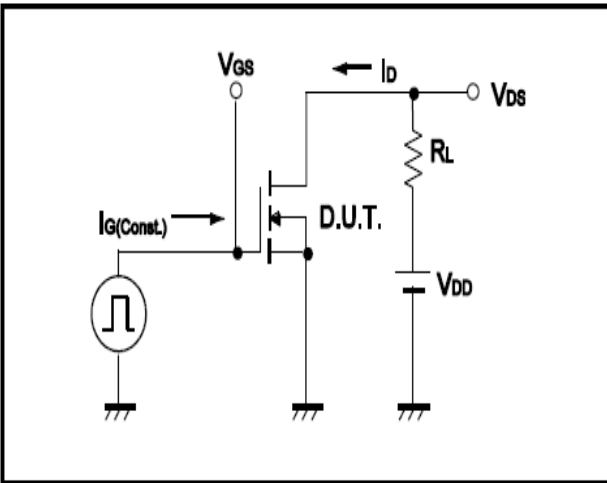


Fig.10 Gate Charge Waveform

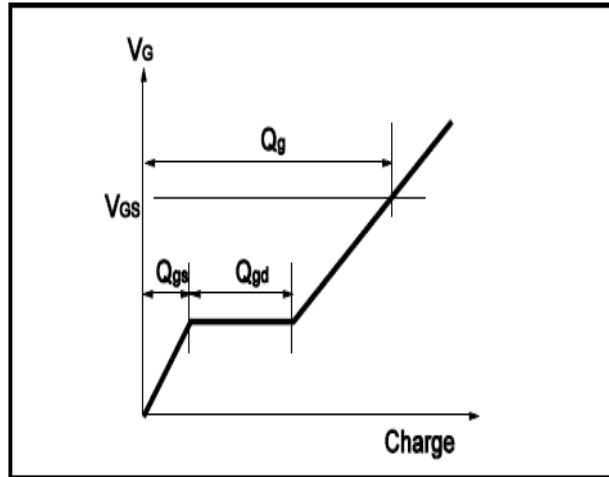


Fig.11 Switching Time Measurement Circuit

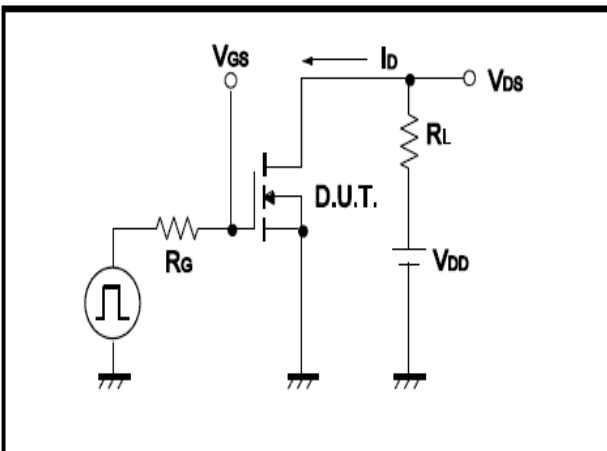
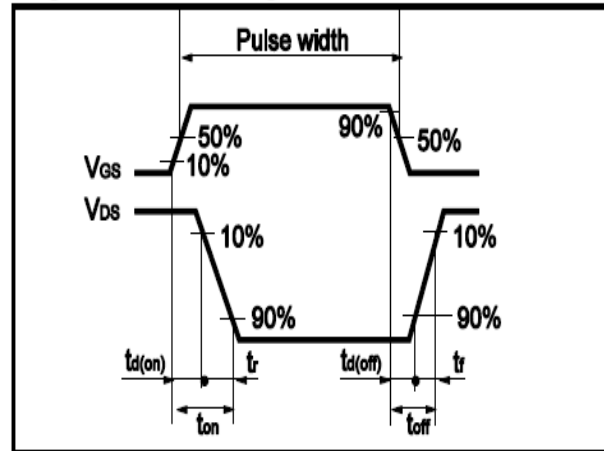


Fig.12 Gate Charge Waveform



•Dimensions (TO-252)

Unit: mm

SYMBOL	min	max	SYMBOL	min	max
A	2.10	2.50	B	0.85	1.25
b	0.50	0.80	b1	0.50	0.90
b2	0.45	0.70	C	0.45	0.70
D	6.30	6.75	D1	5.10	5.50
E	5.30	6.30	e1	2.25	2.35
L1	9.20	10.60	e2	4.45	4.75
L2	0.90	1.75	L3	0.60	1.10
K	0.00	0.23			

